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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

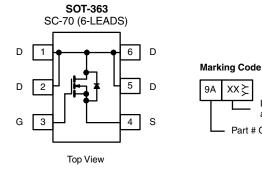
PRODUCT SUMMARY				
V _{DS} (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.140			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.200			
I _D (A)	1.6			
Configuration	Single			

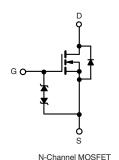
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- AEC-Q101 Qualifiedd
- 100 % R_g Tested
- Typical ESD Protection: 800 V
- Compliant to RoHS Directive 2002/95/EC









ORDERING INFORMATION	
Package	SC-70
Lead (Pb)-free and Halogen-free	SQ1420EEH-T1-GE3

Lot Traceability and Date Code

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	V _{GS} ± 20		
Continuous Drain Current ^a	T _C = 25 °C	- I _D	1.6	A	
	T _C = 125 °C		1.6		
Continuous Source Current (Diode Conduction) ^a		I _S	1.6	^	
Pulsed Drain Current ^b	I _{DM}	6.7			
Maximum Power Dissipation ^b	T _C = 25 °C	0	3.3	W	
	T _C = 125 °C	P_{D}	1.1		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient P	PCB Mount ^c	R _{thJA}	125	°C/W		
Junction-to-Foot (Drain)		R _{thJF}	45	C/VV		

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT	
Static						l .	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \mu A$		60	-	-	\/
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$		-	-	± 500	nA
Gate-Source Leakage		V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	1	mA
		V _{GS} = 0 V	V _{GS} = 0 V V _{DS} = 60 V		-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 60 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 60 V, T _J = 175 °C	-	-	150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	1	-	-	Α
		V _{GS} = 10 V	I _D = 1.2 A	-	0.100	0.140	Ω
Dunin Course On Otata Basistan as		V _{GS} = 10 V	I _D = 1.2 A, T _J = 125 °C	-	-	0.245	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 1.2 A, T _J = 175 °C	-	-	0.308	
		V _{GS} = 4.5 V	I _D = 1 A	-	0.152	0.200	
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 1 A	-	2.9	-	S
Dynamic ^b	<u> </u>						
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	172	215	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	36	45	
Reverse Transfer Capacitance	C _{rss}]		-	24	30	
Total Gate Charge ^c	Qg			-	2.7	4	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V	$V_{DS} = 30 \text{ V}, I_D = 2.8 \text{ A}$	-	0.7	-	nC
Gate-Drain Charge ^c	Q _{gd}	1		-	1.4	-	1
Gate Resistance	Rg	f = 1 MHz		1.1	1.6	2.1	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	12	18	
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V, } R_L = 30 \Omega$ $I_D \cong 1 \text{ A, } V_{GEN} = 4.5 \text{ V, } R_g = 1 \Omega$		-	21	32	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	8	12	
Fall Time ^c	t _f			-	7	11	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed Current ^a	I _{SM}			-	-	6.7	Α
Forward Voltage	V_{SD}	I _F =	-	0.8	1.2	V	

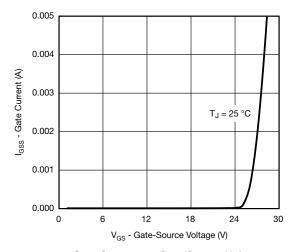
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

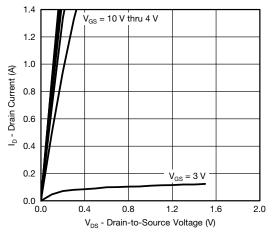
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



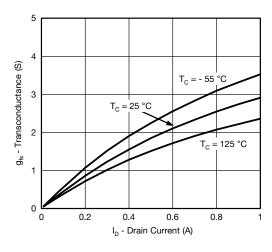
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



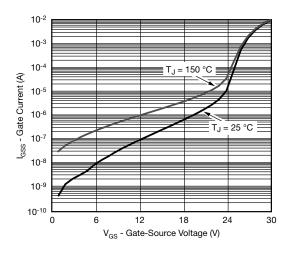
Gate Current vs. Gate-Source Voltage



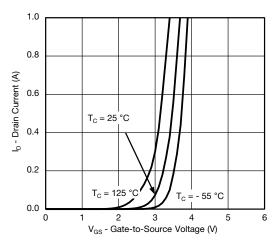
Output Characteristics



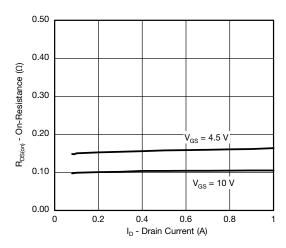
Transconductance



Gate Current vs. Gate-Source Voltage



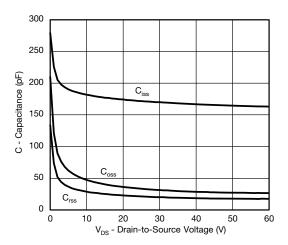
Transfer Characteristics



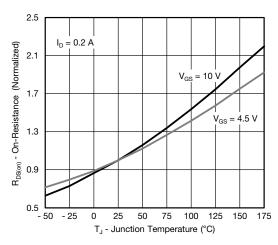
On-Resistance vs. Drain Current



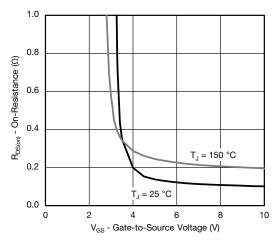
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



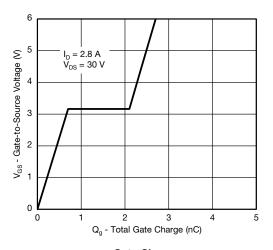
Capacitance



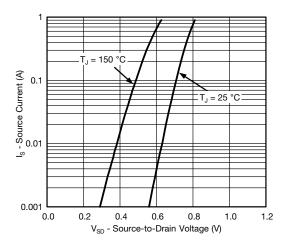
On-Resistance vs. Junction Temperature



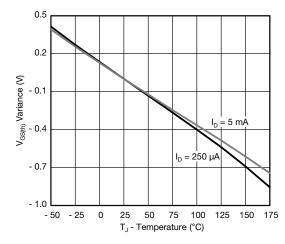
On-Resistance vs. Gate-to-Source Voltage



Gate Charge

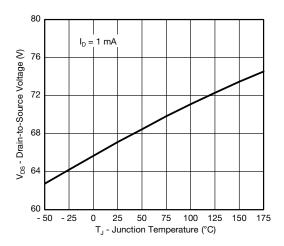


Source Drain Diode Forward Voltage

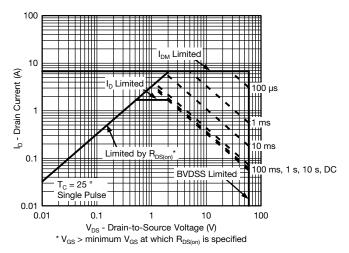


Threshold Voltage

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

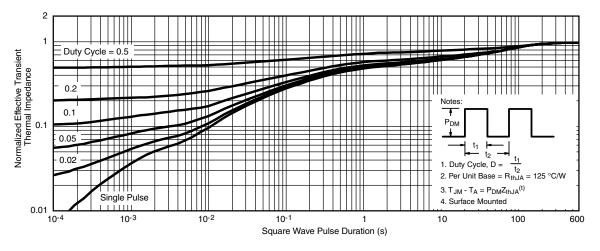


Drain Source Breakdown vs. Junction Temperature

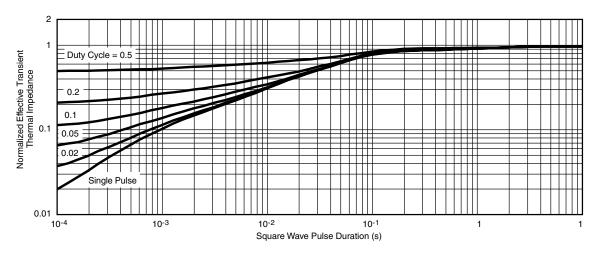


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

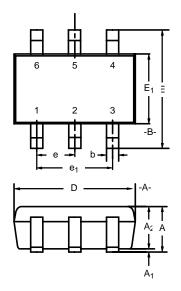
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

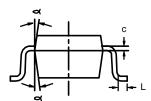
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265730.



SC-70: 6-LEADS



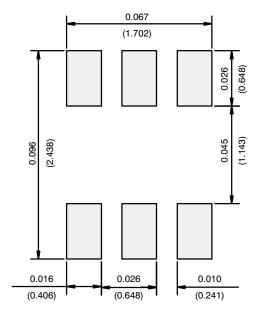


	MILLIMETERS			INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.90	_	1.10	0.035	_	0.043
A_1	_	-	0.10	-	_	0.004
A ₂	0.80	_	1.00	0.031	_	0.039
b	0.15	_	0.30	0.006	_	0.012
С	0.10	_	0.25	0.004	_	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
Е	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
4	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5550						

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RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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